

General Description

This MOSFET developed through advanced trench technology, is designed to minimize on-state resistance, thereby making it suitable for power management and load switching in commercial applications.

Features

- Low $R_{DS(on)}$
- Low Capacitance
- Low Gate Charge
- RoHS Compliant and Halogen-Free

Applications

- Load Switch
- DC-DC Converters
- Synchronous Rectification
- Voltage Regulator Components

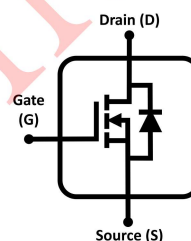
30V N-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	ID
30 V	4.81 mΩ@10 V	57 A
	8.2 mΩ@4.5 V	

PPAK3x3



Pin Configuration



Absolute Maximum Ratings (T_J=25°C, unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{DS}	Drain-Source Voltage		30	V
V_{GS}	Gate-Source Voltage		±20	
I_D	Drain Current-Continuous *A	$T_A=25\text{ }^{\circ}\text{C}$	19	A
		$T_A=70\text{ }^{\circ}\text{C}$	15	
		$T_C=25\text{ }^{\circ}\text{C}$	57	
		$T_C=100\text{ }^{\circ}\text{C}$	36	
I_{DM}	Drain Current-Pulsed *A,B	$T_A=25\text{ }^{\circ}\text{C}$	120	A
I_{AS}	Non-repetitive Avalanche Current *E		19.9	A
E_{AS}	Single Pulse Drain-to-Source Avalanche Energy *E		19.9	mJ
P_D	Maximum Power Dissipation	$T_A=25\text{ }^{\circ}\text{C}$	2.8	W
		$T_C=25\text{ }^{\circ}\text{C}$	24	
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C

Thermal Characteristics

Symbol	Parameter	Conditions	Value	Unit
$R_{\theta JA}$	Junction-to-Ambient *C	Steady State	45	°C/W
$R_{\theta JC}$	Junction-to-Case	Steady State	5.2	°C/W